



NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

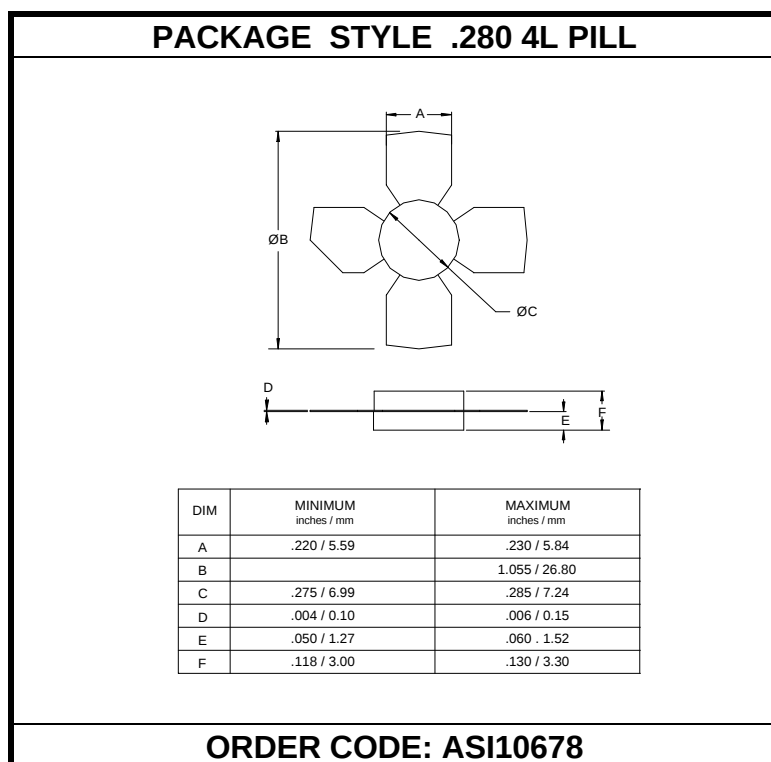
The ASI ULBM2SL is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	0.75 A
V_{CBO}	36 V
V_{CER}	16 V
V_{CES}	36 V
V_{EBO}	4.0 V
P_{DISS}	5.0 W @ $T_C = 25\text{ }^{\circ}\text{C}$
T_J	-65 $^{\circ}\text{C}$ to +200 $^{\circ}\text{C}$
T_{STG}	-65 $^{\circ}\text{C}$ to +150 $^{\circ}\text{C}$
θ_{JC}	35.0 $^{\circ}\text{C/W}$



CHARACTERISTICS $T_C = 25\text{ }^{\circ}\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 25\text{ mA}$	16			V
BV_{CES}	$I_C = 5\text{ mA}$	36			V
BV_{EBO}	$I_E = 1\text{ mA}$	4.0			V
I_{CBO}	$V_{CB} = 15\text{ V}$			1.0	mA
I_{CER}	$V_{CE} = 10\text{ V}$ $R_{BE} = 80\text{ }\Omega$			0.5	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 100\text{ mA}$	40		200	---
C_{ob}	$V_{CB} = 7.5\text{ V}$ $f = 1.0\text{ MHz}$			10	pF
P_G η_C	$V_{CC} = 12.5\text{ V}$ $P_{OUT} = 2.0\text{ W}$ $f = 470\text{ MHz}$	11.5	60		dB %